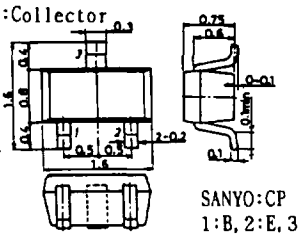
High-h_{FE} High V_{EBO} Transistors

High- hFE, High- VEBO Transistors

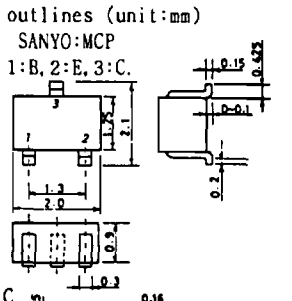
1:Base
2:Emitter
3:Collector

SANYO:SMCP



Case outlines (unit:mm)

SANYO:MCP
1:B, 2:E, 3:C.



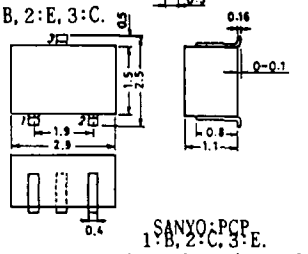
Features

- High hFE (500 to 3200)
- High VEBO ≧15V
- Low saturation voltage (VCE(sat)≦0.5V)
- Very small package permitting audio/video sets to be made smaller, slimmer

Applications

- AF amp
- Driver
- Muting circuit

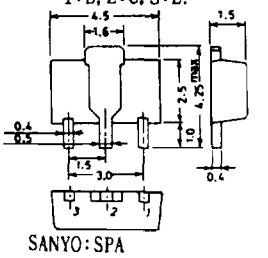
SANYO:CP
1:B, 2:E, 3:C.



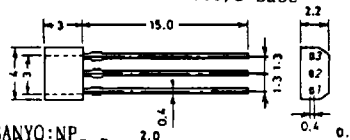
◎:Resistance-Contained (2SC4909:R1=47KΩ, R2=47KΩ)
For PNP, (-) sign is omitted. ※ sign Tc=25℃. ☆ sign Mounted on ceramic board (250mm²×0.8mm).

Type No. ( ):Marking on MCP, CP.	Package	Absolute Maximum Ratings/ Ta=25℃ V_{CBO} (V)	V_{CEO} (V)	V_{EBO} (V)	I_C (A)	P_C (W)	Electrical Characteristics/Ta=25℃ V_{CE} (V)	I_C (mA)	h_{FE}	I_C (mA)	I_B (mA)	$V_{CE(sat)}$ typ (V)	max (V)
2SC4919(DA)	SMCP	25	15	5	0.1	0.15	2	5	800 ~ 3200	10	1	14m	30m
2SA1813(KS)	MCP	30	25	15	0.15	0.15	5	1	500 ~ 1200	50	1	0.15	0.3
2SC4413(GY)		60	50	15	0.1	0.15	5	10	800 ~ 3200	50	1	0.1	0.5
2SC4851(YT)		25	15	5	0.1	0.2	2	5	800 ~ 3200	10	1	14m	30m
2SC4909(JN)◎		25	20	10	0.1	0.2	2	5	200	2	0.2	10m	30m
2SA1434(FL)	CP	60	50	15	0.1	0.2	5	10	500 ~ 1200	50	1	0.2	0.5
2SC3689(GY)									800 ~ 3200			0.1	
2SA1814(KS)		30	25	15	0.15	0.2	5	1	500 ~ 1200	50	1	0.15	0.3
2SC3661(FY)		30	25	15	0.3	0.2	5	10	800 ~ 3200	200	4	0.12	0.5
2SC4852(YT)		25	15	5	0.1	0.25	2	5	800 ~ 3200	10	1	14m	30m
2SA1766(AL)	PCP	30	25	15	0.3	☆1.3	5	10	500 ~ 1200	200	4	0.12	0.5
2SC3650(CF)		30	25		1.2	☆1.5	5	500	800 ~ 3200	500	10	0.12	0.5
2SC3651(CG)		120	100		0.2	☆1.3	5	10	500 ~ 2000	100	2	0.15	0.5
2SC4390(CJ)		20	10		2	☆1.3	2	500	800 ~ 3200	1000	20	0.11	0.3
2SC4705(CP)		60	50		0.2	☆1.3	5	100	800 ~ 3200	100	2	0.12	0.5
2SC5069(CU)		30	25		2	☆1.5	5	500	800 ~ 3200	1000	20	0.15	
2SC3576	SPA	30	25		0.3	0.3	5	10	800 ~ 3200	200	4	0.12	
2SC3820		60	50		0.1	0.3	5	10	800 ~ 3200	50	1	0.1	
2SA1435	NP	30	25		0.3	0.6	5	10	500 ~ 1200	200	4	0.18	
2SC3068									800 ~ 3200			0.12	
2SA1436		60	50		0.2	0.6	5		500 ~ 1200			0.2	
2SC3069								10	800 ~ 3200	100	2	0.18	
2SA1437		120	100		50m	0.5	5	10	400 ~ 1000	10	0.2	0.18	
2SC3495									500 ~ 2000			0.1	
2SC4204		30	25		0.7	0.6	5	50	800 ~ 3200	500	10	0.15	
2SA1562	TP	30	25		1.2	※15	5	100	500 ~ 1200	500	10	0.1	
2SC5155		50	20		3	※20	2	500	800 ~ 3200	2000	20	0.15	
2SC3070	MP	30	25		1.2	1	5	500	800 ~ 3200	500	10	0.12	
2SC3071		120	100		0.2	1	5	10	500 ~ 2000	100	2	0.15	
2SC4736	FLP	80	60		2	1.5	5	500	800 ~ 3200	1000	20	0.2	
2SC5070		30	25		2	1.5	5	500	800 ~ 3200	1000	20	0.15	
2SA1692	TO-126LP	30	25		2	※15	5	100	500 ~ 1200	1000	20	0.15	
2SC3807								500	800 ~ 3200				
2SC3808		80	60		2	※15	5	500	800 ~ 3200	1000	20	0.2	

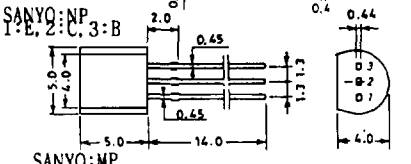
SANYO:PCP
1:B, 2:C, 3:E.



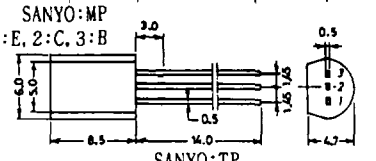
SANYO:SPA
1:Emitter, 2:Collector, 3:Base



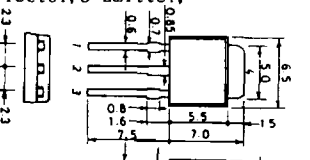
SANYO:NP
1:E, 2:C, 3:B



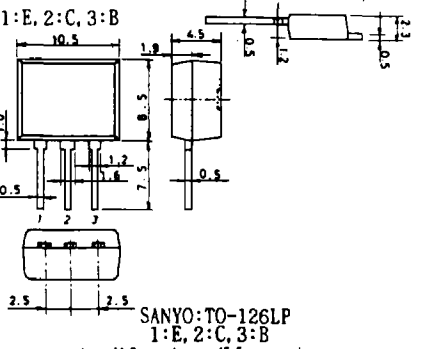
SANYO:MP
1:E, 2:C, 3:B



SANYO:TP
1:Base, 2:Collector, 3:Emitter,
4:Collector



SANYO:FLP
1:E, 2:C, 3:B



High-VEBO Transistors

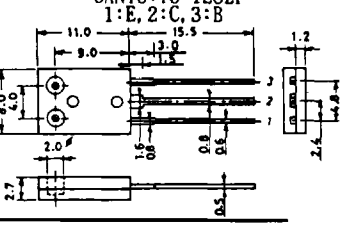
Features

- Highly resistant to surge voltage because of high VEBO.
- Highly resistant to breakdown because of wide ASO.

For PNP, (-) sign is omitted.

2SA1687(D)	MCP	60	50	15	0.15	0.15	6	1	135 ~ 600	50	5	0.25	0.5
2SC4446(H)												0.15	
2SC4694(WT)		50	20	25	0.5	0.15	5	10	300 ~ 1200	100	2	0.12	
2SA1252(D-)	CP	60	50	15	0.15	0.2	6	1	100 ~ 560	50	5	0.2	
2SC3134(H-)												0.15	
2SC4695(WT)		50	20	25	0.5	0.25	5	10	300 ~ 1200	100	2	0.12	
2SA1253	SPA	60	50	15	0.2	0.25	6	1	100 ~ 560	50	5	0.2	
2SC3135												0.15	
2SA1246	NP	60	50	15	0.15	0.4	6	1	100 ~ 560	50	5	-	
2SC3114												-	
2SC3792		50	20	25	0.5	0.5	5	10	300 ~ 1200	100	2	0.12	

SANYO:TO-126LP
1:E, 2:C, 3:B



These specifications are subject to change without notice.